NSN 5961-01-041-0283

Semiconductor Device Set - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-041-0283 **Inclosure Material:** Metal all transistor **Overall Length:** 0.170 inches all transistor and 0.210 inches all transistor **Terminal Length:** 1.500 inches all transistor **Overall Diameter:** 0.209 inches all transistor and 0.230 inches all transistor **Internal Configuration:** Field effect all transistor **Channel Polarity And Control Type (non-core):** P-channel junction type all transistor Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-18 all transistor **Component Function Relationship:** Matched **Component Name And Quantity:** 2 transistor **Mounting Method:** Terminal all transistor **Terminal Circle Diameter:** 0.100 inches all transistor **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, gate-to-source, with all other terminals short-circuited to source all transistor and 4.0 gate to source cutoff voltage all transistor **Current Rating Per Characteristic:** 4.50 milliamperes zero-gate-voltage source current megawatts all transistor **Power Rating Per Characteristic:** 300.0 milliwatts small-signal input power, common-collector absolute all transistor **Terminal Type And Quantity:** 3 uninsulated wire lead all transistor Shelf Life: N/a **Unit Of Measure:**

Fiig:

No

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Demilitarization: